## PATENT APPLICATION

Attorney Docket No.: 2000.006.00/US

PTO/SB/08A (10-01)
Approved for use through 10/31/2002. OMB 0651-0031
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

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Substitute for form 1449A/PTO			Complete if Kn wn		
		Application Number	19609185		
			Filing Date	June 26, 2003	
			First Named Inventor	Andrew E. Horch	
FORM PTO-1449 (Modified)		Art Unit			
MANY SH	EETS AS NEC	ESSARY)	Examiner Name		
1	OF	3	Attorney Docket Number	2000.006.00/US	
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	U.S. PATENT DOCUMENTS						
Examiner	Cite	Document Number	Publication Date	Name of Patentee or	Pages, Columns, Lines, Where		
Initials.		Number- Kind Code (# known)	MM-DD-YYYY	Applicant of Cited Document	Relevant Passages or Relevant Figures Appear		
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Examiner Initials	Cite No.1	Foreign Patent Document  Country Code3-Number 4 - Kind Code s (# known)	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	Ts			

Examiner Signature Date Considered 9	-0404	
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SHEET	2	OF	3	Attorney Docket Number	2000.006.00/US	

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		Number- Khd Code (# known)	MM-DD-YYYY	Applicant of Cited Document	Relevant Passages or Relevant Figures Appear			
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Examiner Signature	aga	Date Considered	9-01-04

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<sup>1</sup> Applicant's unique citation designation number (optional), 2 See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04, 3 Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3), 4 For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document, 5 Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible, 6 Applicant is to place a check mark here if English language Translation is attached.

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(USE AS MANY SHEETS AS NECESSARY)		Examiner Name				
SHEET	3	OF	3	Attorney Docket Number	2000.006.00/US	

		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS	
Examiner Initials•	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T2
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